

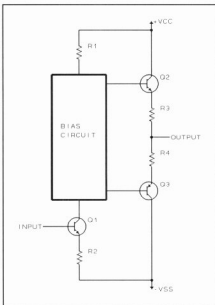
# Improved Vbe Doubler

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This circuit is an improved version of an old  $V_{BE}$  doubler. It is useful for class AB amplifiers which are of the topology as shown in Figure 1. This type of amplifier needs a bias circuit for  $Q_1$  and  $Q_2$  such that there is a constant voltage between their bases. Without a controlled bias voltage, the quiescent collector currents of  $Q_1$  and  $Q_2$  may be excessive, causing thermal failure, or insufficient, causing crossover distortion. It is desirable that this voltage have a similar temperature coefficient to the combined  $V_{BE}$  drop of  $Q_1$  and  $Q_2$ . All four bias circuits shown in Figure 2 are temperature compensated, but only one of them has good regulation over current.

Figure 2a is the simplest, just two series diodes. Figure 2b is the common  $V_{BE}$  multiplier set up as a doubler. Figure 2c is a two transistor approach, and finally Figure 2d is the improved circuit with better performance.



The voltage output of the circuit in Figure 1, ignoring base currents, is given as

$$V_o = V_{BE2} + V_{BE1} - I_b R_{14}$$

The current through  $Q_{13}$  does not change too much, so most of the change in output voltage comes from  $Q_{14}$ 's B-E junction. To calculate  $R_{14}$  in Figure 2d, find  $V_{BE}$  of the transistor at two points, minimum and maximum input currents. Set the voltage drop across  $R_{14}$  to be equal to the  $V_{BE}$  drop.

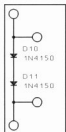


Figure 2a.

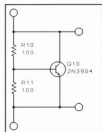


Figure 2b.

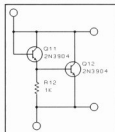


Figure 2c.

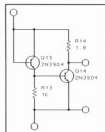


Figure 2d.

For example, the Motorola data sheet for a 2N3904 transistor gives a  $V_{BE}$  of 0.71V at 10mA and 0.87V at 100mA. This is a difference of 0.16V. The same drop across  $R_{14}$  for a change in current from 10mA to 100mA would require 1.8 $\Omega$ .

All four bias circuits were simulated in SPICE to measure their dc performance. Figure 3 displays the results. Only the new improved circuit performed well over the input current range. From 10mA to 100mA, the change in output voltages were circuit A: 340mV, circuit B: 740mV, circuit C: 190mV, and circuit D: 30mV.

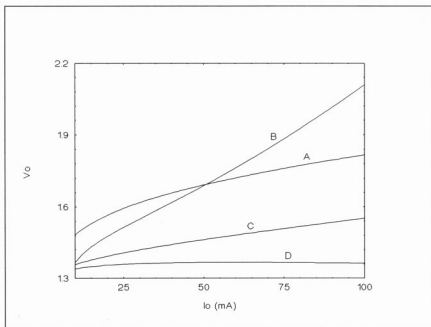


Figure 3.